TMS 4108 NL
8,192-BIT DYNAMIC RANDOM-ACCESS MEMORY

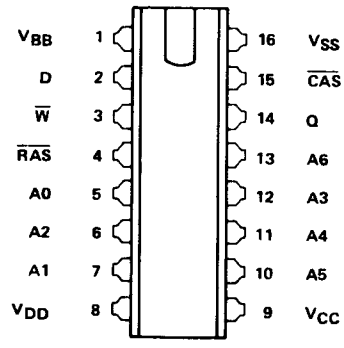
AUGUST 1979

- 8,192 X 1 Organization
- 10% Tolerance on All Supplies
- All Inputs Including Clocks TTL-Compatible
- Unlatched Three-State Fully TTL-Compatible Output
- 3 Performance Ranges:

	ACCESS TIME ROW ADDRESS (MAX)	ACCESS TIME COLUMN ADDRESS (MAX)	READ OR WRITE CYCLE (MIN)	READ, MODIFY-WRITE† CYCLE (MIN)
TMS 4108-15	150 ns	100 ns	375 ns	375 ns
TMS 4108-20	200 ns	135 ns	375 ns	375 ns
TMS 4108-25	250 ns	165 ns	410 ns	515 ns

- Page-Mode Operation for Faster Access Time
- Common I/O Capability with "Early Write" Feature
- Low-Power Dissipation
  - Operating . . . 462 mW (max)
  - Standby . . . 20 mW (max)
- 1-T Cell Design, N-Channel Silicon-Gate Technology
- 16-Pin 300-Mil (7,62 mm) Package Configuration

16-PIN PLASTIC
DUAL-IN-LINE PACKAGE
(TOP VIEW)



PIN NOMENCLATURE			
A0-A6	Address Inputs	$\overline{W}$	Write Enable
$\overline{CAS}$	Column address strobe	V_{BB}	−5-V power supply
D	Data input	V_{CC}	+5-V power supply
Q	Data output	V_{DD}	+12-V power supply
$\overline{RAS}$	Row address strobe	V_{SS}	0 V ground

description

The TMS 4108 series is composed of monolithic high-speed Dynamic 8,192-bit MOS random-access memories organized as 8,192 one-bit words and employing single-transistor storage cells and N-channel silicon-gate technology.

All input and outputs are compatible with Series 74 TTL circuits including clocks, Row Address Strobe ($\overline{RAS}$ or R), and Column Address Strobe ($\overline{CAS}$ or C). All address lines (A0 through A6) and the data input (D) are latched on chip to simplify system design. Data out (Q) is unlatched to allow greater system flexibility.

Typical power dissipation is less than 350 milliwatts active and 6 milliwatts during standby (V_{CC} is not required during standby operation). To retain data, only 10 milliwatts average power is required which includes the power consumed to refresh the contents of the memory.

There are two array-select versions of the TMS 4108, each offered in the three speed ranges indicated above and in plastic (NL suffix) packaging only. The left-array version is indicated by "0" following the type number (e.g., TMS 4108-15 NL0), and the right-array version is indicated by "1" (e.g., TMS 4108-25 NL1). Each 8K X 1 version is in a 16-pin dual-in-line package rated for operation from 0°C to 70°C.

operation

address (A0 through A6)

Thirteen address bits are required to decode 1 of 8,192 storage cell locations. Seven row-address bits are set up on pins A0 through A6 and latched onto the chip by the row-address strobe ($\overline{RAS}$). Then the seven column-address bits are set up on pins A0 through A6 and latched onto the chip by the column-address strobe ($\overline{CAS}$). If the type number is followed by a "0", then column address input A0 must always be at V_{IL}; if it is followed by a "1", column address A0 must always be at V_{IH}. All addresses must be stable on or before the falling edges of $\overline{RAS}$ and $\overline{CAS}$. $\overline{RAS}$ is similar to a chip enable in that it activates the sense amplifiers as well as the row decoder. $\overline{CAS}$ is used as a chip select activating the column decoder and the input and output buffers.

†The term "read-write cycle" is sometimes used as an alternative title to "read-modify-write cycle".

PRELIMINARY DATA SHEET:
Supplementary data will be published at a later date.

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write enable ($\overline{W}$)

The read or write mode is selected through the write enable ($\overline{W}$) input. A logic high on the $\overline{W}$ input selects the read mode, and a logic low selects the write mode. The write enable terminal can be driven from standard TTL circuits without a pull-up resistor. The data input is disabled when the read mode is selected. When $\overline{W}$ goes low prior to $\overline{CAS}$, data-out will remain in the high-impedance state for the entire cycle permitting common I/O operation.

data-in (D)

Data is written during a write or read-modify write cycle. The latter falling edge of $\overline{CAS}$ or $\overline{W}$ strobes data into the on-chip data latch. This latch can be driven from standard TTL circuits without a pull-up resistor. In an early write cycle $\overline{W}$ is brought low prior to $\overline{CAS}$, and the data is strobed in by $\overline{CAS}$ with setup and hold times referenced to this signal. In a delayed write or read-modify write cycle, $\overline{CAS}$ will already be low, thus the data will be strobed in by $\overline{W}$ with setup and hold times referenced to this signal.

data-out (Q)

The three-state output buffer provides direct TTL compatibility (no pull-up resistor required) with a fan-out of two Series 74 TTL loads. Data-out is the same polarity as data-in. The output is in the high-impedance (floating) state until $\overline{CAS}$ is brought low. In a read cycle the output goes active after the enable time interval $t_{a(C)}$ that begins with the negative transition of $\overline{CAS}$ as long as $t_{a(R)}$ is satisfied. The output becomes valid after the access time has elapsed and remains valid while $\overline{CAS}$ is low; $\overline{CAS}$ going high returns it to a high-impedance state. In an early write cycle, the output is always in the high-impedance state. In a delayed write or read-modify-write cycle, the output will follow the sequence for the read cycle.

refresh

A refresh operation must be performed at least every two milliseconds to retain data. Since the output buffer is in the high-impedance state unless $\overline{CAS}$ is applied, the $\overline{RAS}$-only refresh sequence avoids any output during refresh. Strobing each of the 128 row addresses (A0 through A6) with $\overline{RAS}$ causes all bits in each row to be refreshed. $\overline{CAS}$ remains high (inactive) for this refresh sequence, thus conserving power.

page mode

Page-mode operation allows effectively faster memory access by keeping the same row address and strobing successive column addresses onto the chip. Thus, the time required to set up and strobe sequential row addresses on the same page is eliminated. To extend beyond the 64 column locations on a single RAM, the row address and $\overline{RAS}$ is applied to multiple 8K RAMs. $\overline{CAS}$ is decoded to select the proper RAM.

power-up

V_{BB} must be applied to the device either before or at the same time as the other supplies and removed last. Failure to observe this precaution will cause dissipation in excess of the absolute maximum ratings due to internal forward bias conditions. This also applies to system use, where failure of the V_{BB} supply must immediately shut down the other supplies. After power up, eight memory cycles must be performed to achieve proper device operation.

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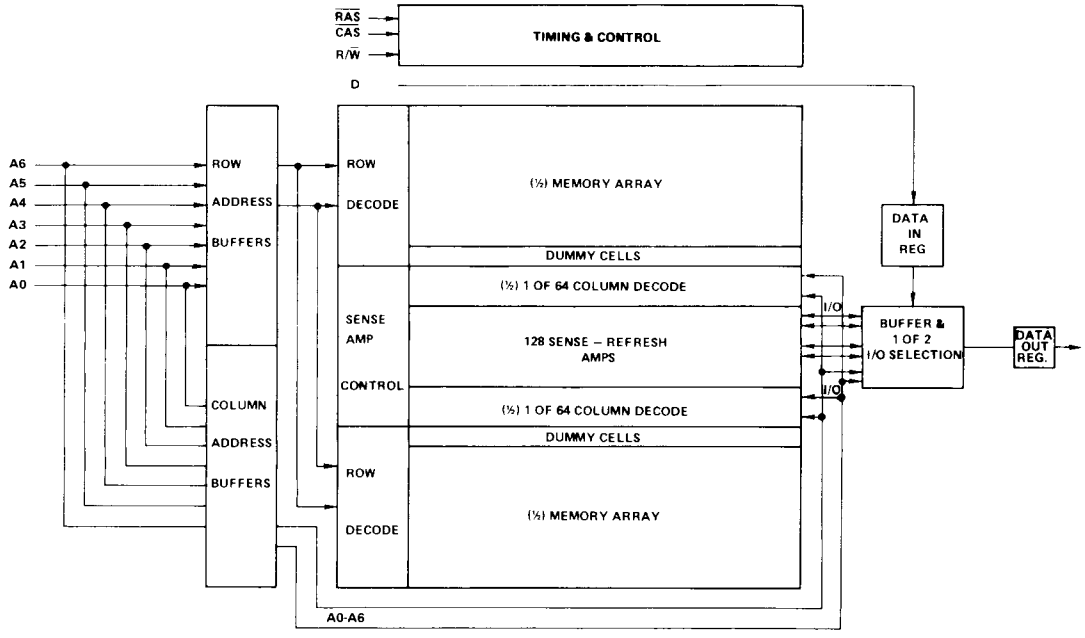
functional block diagram



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)*

Voltage on any pin (see Note 1)	−0.5 to 20 V
Voltage on V_{CC}, V_{DD} supplies with respect to V_{SS}	−1 to 15 V
Short circuit output current	50 mA
Power dissipation	1 W
Operating free-air temperature range	0°C to 70°C
Storage temperature range	−65°C to 150°C

NOTE 1: Under absolute maximum ratings, voltage values are with respect to the most-negative supply voltage, V_{BB} (substrate), unless otherwise noted. Throughout the remainder of this data sheet, voltage values are with respect to V_{SS}.

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions" section of this specification is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

PARAMETER		MIN	NOM	MAX	UNIT
Supply voltage, V_{BB}		−4.5	−5	−5.5	V
Supply voltage, V_{CC}		4.5	5	5.5	V
Supply voltage, V_{DD}		10.8	12	13.2	V
Supply voltage, V_{SS}			0		V
High-level input voltage, V_{IH}	All inputs except RAS, CAS, WRITE	2.4		7	V
	RAS, CAS, WRITE	2.7		7	
Low-level input voltage, V_{IL}		−1†	0	0.8	V
Refresh time, $t_{refresh}$				2	ms
Operating free-air temperature, T_A		0		70	°C

†The algebraic convention where the more negative limit is designated as minimum is used in this data sheet for logic voltage levels and time intervals.

electrical characteristics over full ranges of recommended operating conditions (unless otherwise noted)

PARAMETERS		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = −5 mA	2.4			V
V_{OL}	Low-level output voltage	I_{OL} = 4.2 mA			0.4	V
I_I	Input current (leakage)	V_I = 0 V to 7 V, All other pins = 0 V except V_{BB} = −5 V			±10	μA
I_O	Output current (leakage)	V_O = 0 to 5.5 V, $\overline{CAS}$ high			±10	μA
I_{BB1}	Average operating current during read or write cycle	Minimum cycle time		50	200	μA
I_{CC1}*					4	mA
I_{DD1}				27	35	mA
I_{BB2}	Standby current	After 1 memory cycle $\overline{RAS}$ and $\overline{CAS}$ high		10	100	μA
I_{CC2}					±10	μA
I_{DD2}				0.5	1.5	mA
I_{BB3}	Average refresh current	Minimum cycle time $\overline{RAS}$ cycling, $\overline{CAS}$ high		50	200	μA
I_{CC3}					±10	μA
I_{DD3}				20	27	mA
I_{BB4}	Average page-mode current	Minimum cycle time $\overline{RAS}$ low, $\overline{CAS}$ cycling		50	200	μA
I_{CC4}*					4	μA
I_{DD4}				20	27	mA

*V_{CC} is applied only to the output buffer, so I_{CC} depends on output loading. Output loading is two standard TTL loads.

capacitance over recommended supply voltage range and operating free-air temperature range, f = 1 MHz

PARAMETER		TYP†	MAX	UNIT
$C_{i(A)}$	Input capacitance, address inputs	4	5	pF
$C_{i(D)}$	Input capacitance, data input	4	5	pF
$C_{i(RC)}$	Input capacitance, strobe inputs	8	10	pF
$C_{i(W)}$	Input capacitance, write enable input	8	10	pF
C_o	Output capacitance	5	7	pF

switching characteristics over recommended supply voltage range and operating free-air temperature range

PARAMETER		TEST CONDITIONS	ALTERNATE SYMBOL	TMS 4116-15		TMS 4116-20		TMS 4116-25		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
$t_{a(C)}$	Access time from column address strobe	C_L = 100 pF, Load = 2 Series 74 TTL gates	t_{CAC}		100		135		165	ns
$t_{a(R)}$	Access time from row address strobe	t_{RLCL} = MAX, C_L = 100 pF, Load = 2 Series 74 TTL gates	t_{RAC}		150		200		250	ns
t_{PXZ}	Output disable time	C_L = 100 pF, Load = 2 Series 74 TTL gates	t_{OFF}	0	40	0	50	0	60	ns

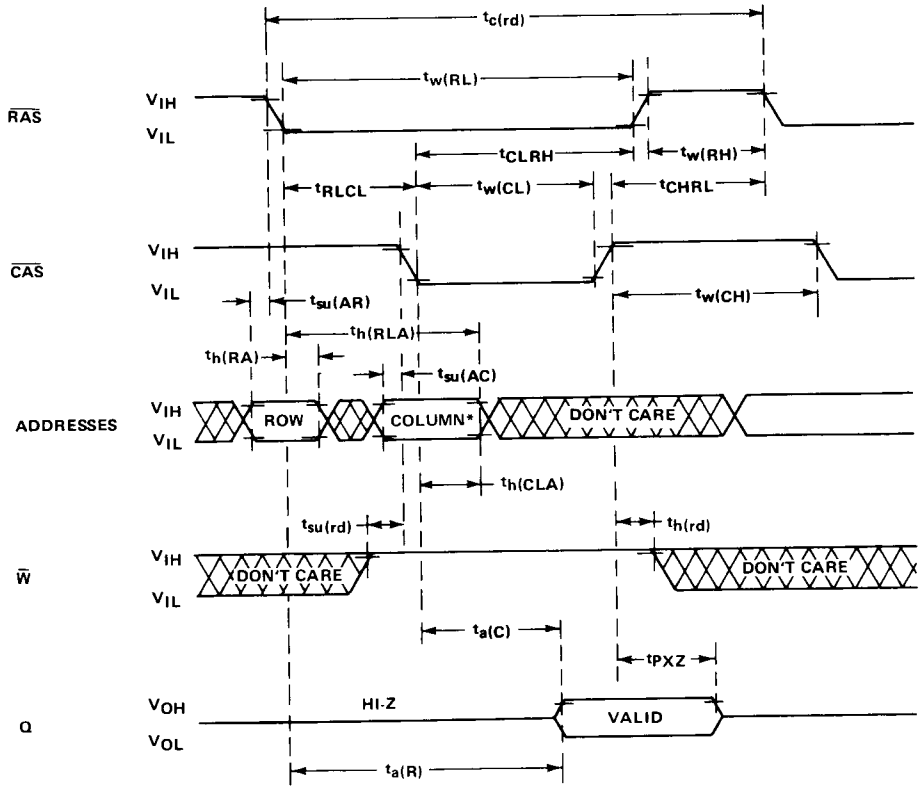
†All typical values are at T_A = 25°C and nominal supply voltages.

timing requirements over recommended supply voltage range and operating free-air temperature range

PARAMETER		ALTERNATE SYMBOL	TMS 4108-15		TMS 4108-20		TMS 4108-25		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
$t_{c(P)}$	Page mode cycle time	t_{PC}	170		225		275		ns
$t_{c(rd)}$	Read cycle time	t_{RC}	375		375		410		ns
$t_{c(W)}$	Write cycle time	t_{WC}	375		375		410		ns
$t_{c(RW)}$	Read-modify-write cycle time	t_{RWC}	375		375		515		ns
$t_{w(CH)}$	Pulse width, column address strobe high (precharge time)	t_{CP}	60		80		100		ns
$t_{w(CL)}$	Pulse width, column address strobe low	t_{CAS}	100	10,000	135	10,000	165	10,000	ns
$t_{w(RH)}$	Pulse width, row address strobe high (precharge time)	t_{RP}	100		120		150		ns
$t_{w(RL)}$	Pulse width, row address strobe low	t_{RAS}	150	10,000	200	10,000	250	10,000	ns
$t_{w(W)}$	Write pulse width	t_{WP}	45		55		75		ns
t_T	Transition times (rise and fall) for $\overline{RAS}$ and $\overline{CAS}$	t_T	3	35	3	50	3	50	ns
$t_{su(AC)}$	Column address setup time	t_{ASC}	−10†		−10†		−10†		ns
$t_{su(AR)}$	Row address setup time	t_{ASR}	0		0		0		ns
$t_{su(D)}$	Data setup time	t_{DS}	0		0		0		ns
$t_{su(rd)}$	Read command setup time	t_{RCS}	0		0		0		ns
$t_{su(WCH)}$	Write command setup time before $\overline{CAS}$ high	t_{CWL}	60		80		100		ns
$t_{su(WRH)}$	Write command setup time before $\overline{RAS}$ high	t_{RWL}	60		80		100		ns
$t_{h(CLA)}$	Column address hold time after $\overline{CAS}$ low	t_{CAH}	45		55		75		ns
$t_{h(RA)}$	Row address hold time	t_{RAH}	20		25		35		ns
$t_{h(RLA)}$	Column address hold time after $\overline{RAS}$ low	t_{AR}	95		120		160		ns
$t_{h(RLC)}$	$\overline{CAS}$ hold time after $\overline{RAS}$ low	t_{CSH}	150		200		250		ns
$t_{h(CLD)}$	Data hold time after $\overline{CAS}$ low	t_{DH}	45		55		75		ns
$t_{h(RLD)}$	Data hold time after $\overline{RAS}$ low	t_{DHR}	95		120		160		ns
$t_{h(WLD)}$	Data hold time after $\overline{W}$ low	t_{DH}	45		55		75		ns
$t_{h(rd)}$	Read command hold time	t_{RCH}	0		0		0		ns
$t_{h(CLW)}$	Write command hold time after $\overline{CAS}$ low	t_{WCH}	45		55		75		ns
$t_{h(RLW)}$	Write command hold time after $\overline{RAS}$ low	t_{WCR}	95		120		160		ns
t_{CHRL}	Delay time, column address strobe high to row address strobe	t_{CRP}	−20†		−20†		−20†		ns
t_{CLRH}	Delay time, column address strobe low to row address strobe high	t_{RSH}	100		135		165		ns
t_{CLWL}	Delay time, column address strobe low to $\overline{W}$ low (read, modify-write cycle only)	t_{CWD}	70		95		125		ns
t_{rf}	Refresh time interval	t_{REF}		2		2		2	ms
t_{RLCL}	Delay time, row address strobe low to column address strobe low (maximum value specified only to guarantee access time)	t_{RCD}	20	50	25	65	35	85	ns
t_{RLWL}	Delay time, row address strobe low to $\overline{W}$ low (read, modify-write cycle only)	t_{RWD}	120		160		200		ns
t_{WLCL}	Delay time, $\overline{W}$ low to column address strobe low (early write cycle)	t_{WCS}	−20†		−20†		−20†		ns

†The algebraic convention where the more negative limit is designated as minimum is used on this data sheet for logic voltage levels and time invervals.

read cycle timing



*For Column Address:
A0 must be at V_{IL} for TMS 4108-0
A0 must be at V_{IH} for TMS 4108-1

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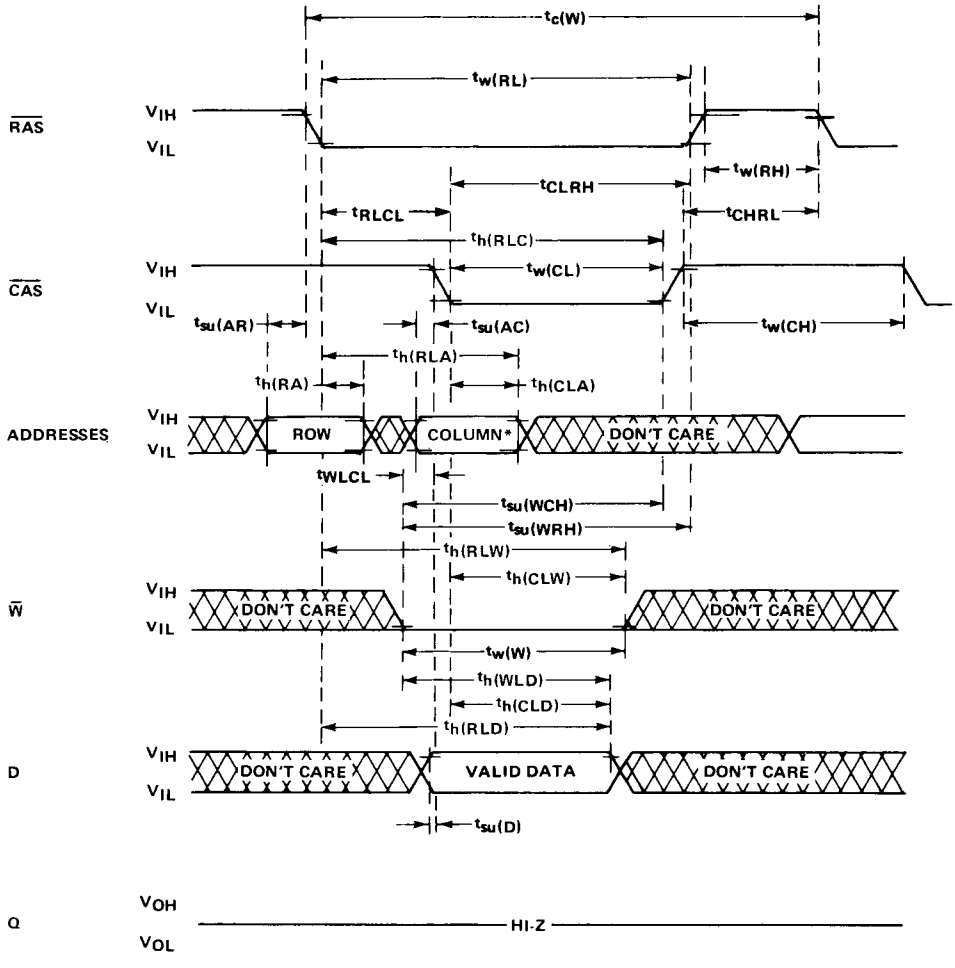
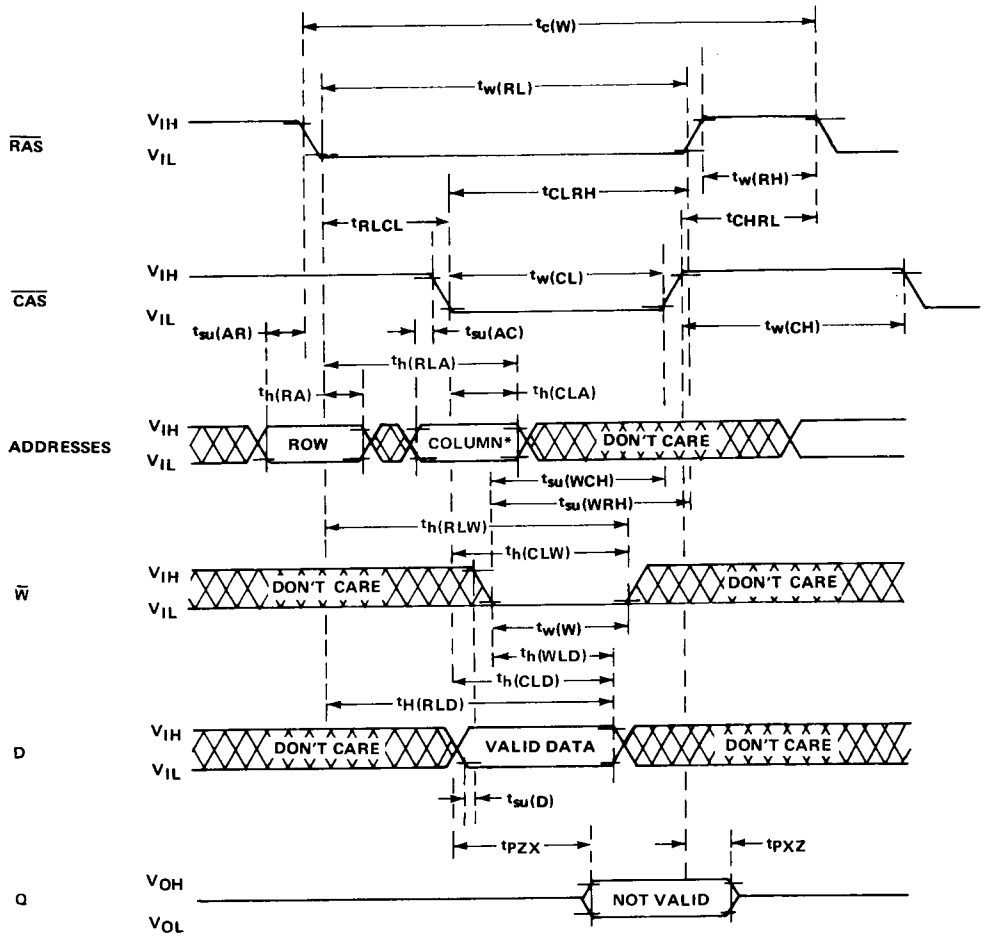
early write cycle timing



*For Column Address:
A0 must be at V_{IL} for TMS 4108-0
A0 must be at V_{IH} for TMS 4108-1

write cycle timing



*For Column Address:
A0 must be at V_{IL} for TMS 4108-0
A0 must be at V_{IH} for TMS 4108-1

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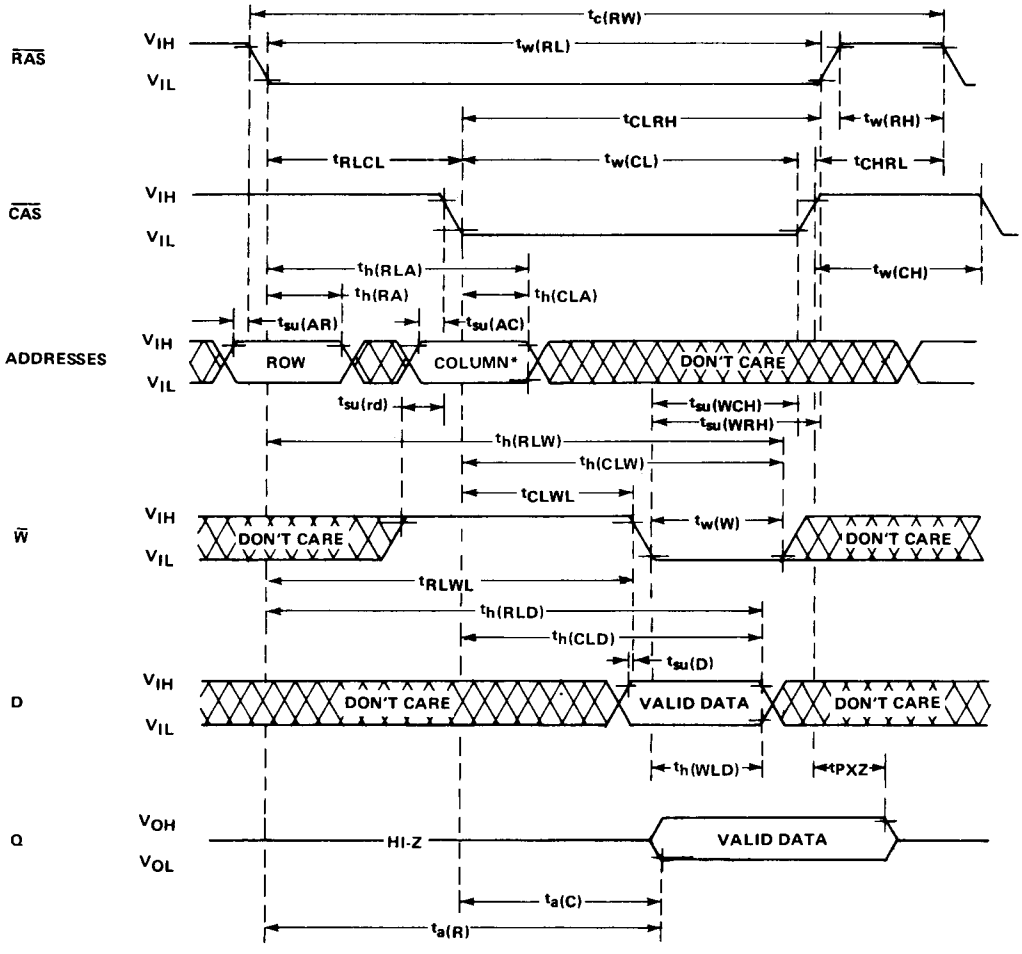
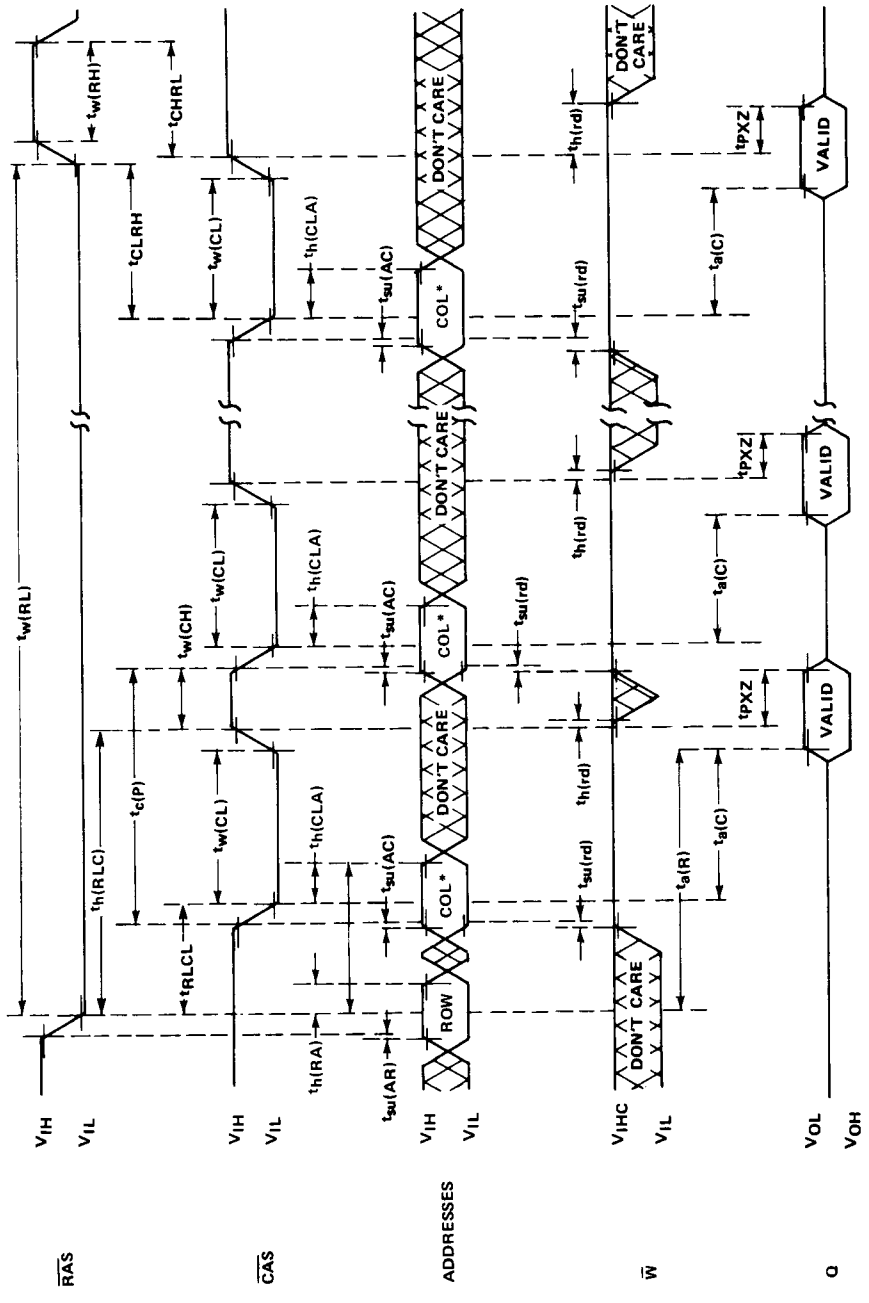
read-write/read-modify-write cycle timing

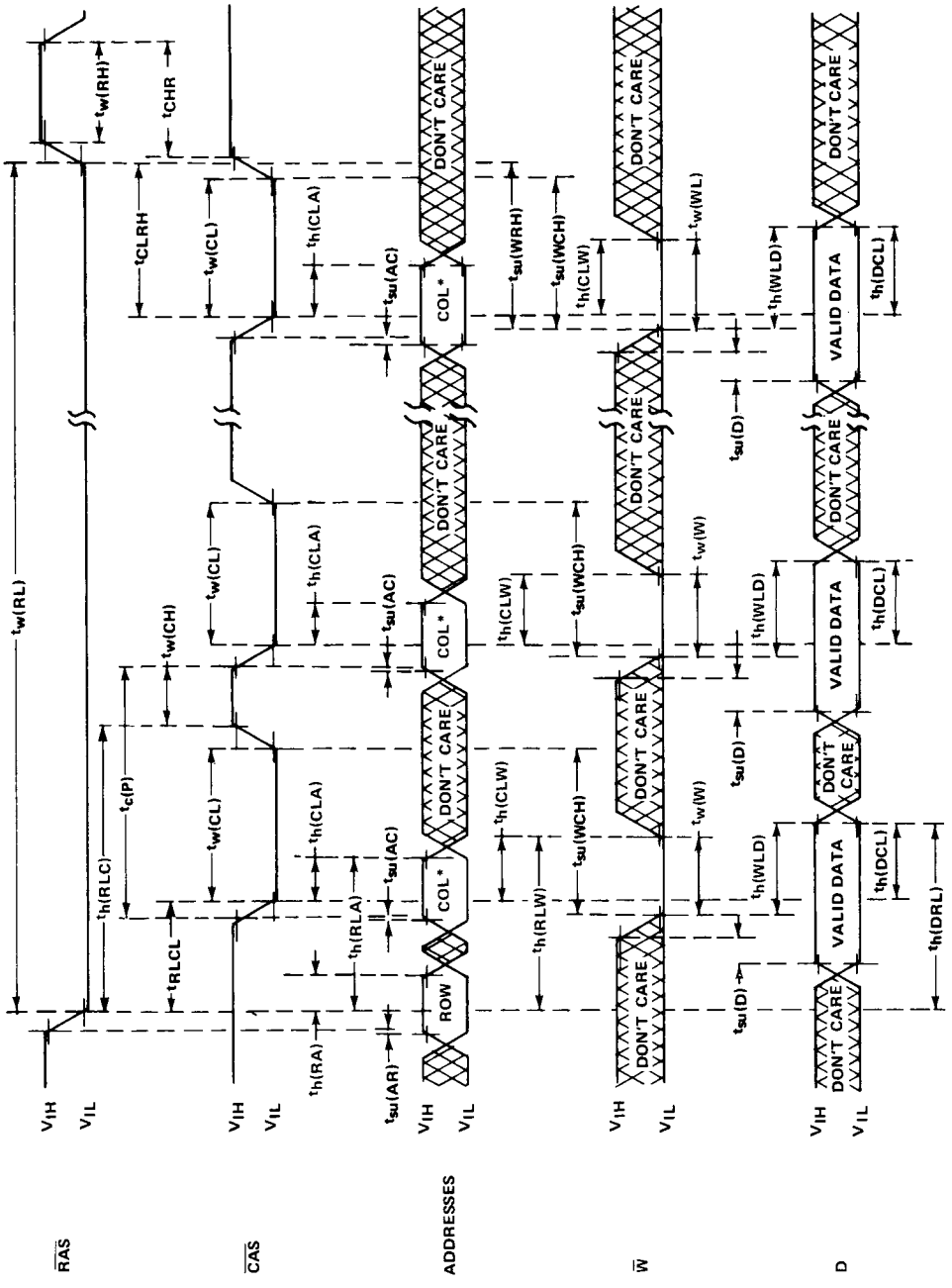


*For Column Address:
A0 must be at V_{IL} for TMS 4108-0
A0 must be at V_{IH} for TMS 4108-1

page-mode read cycle timing

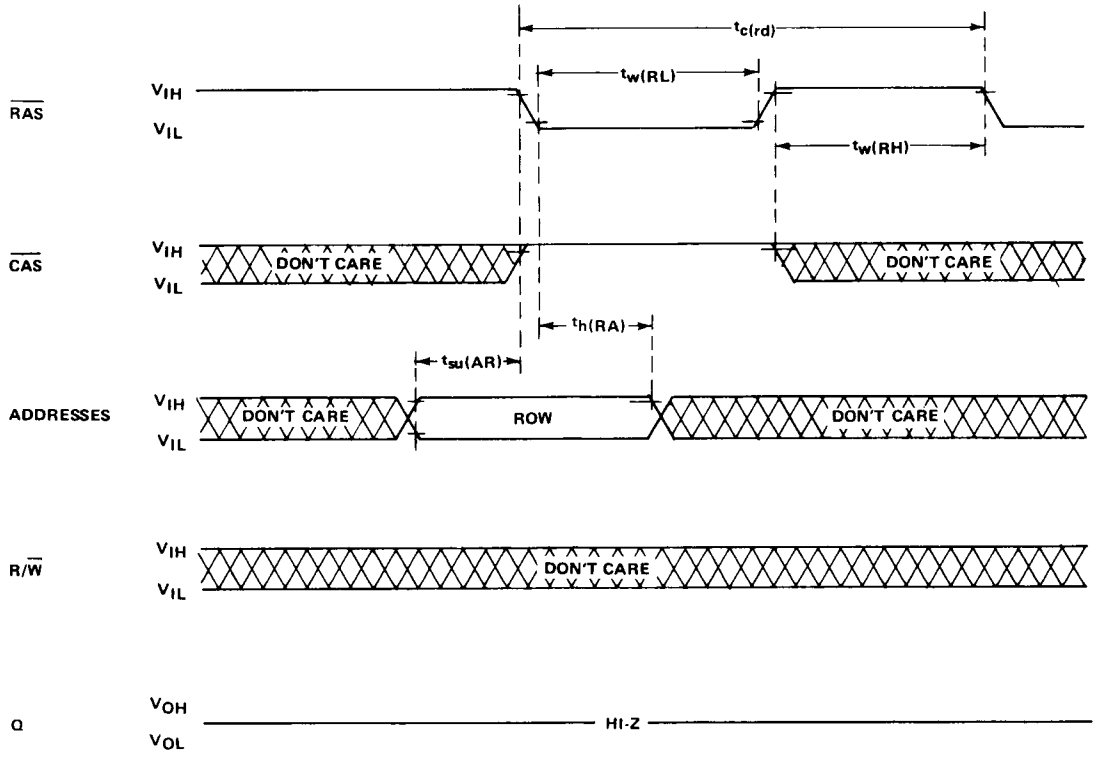


page-mode write cycle timing



*For Column Address:
A0 must be at V_{IL} for TMS 4108-0
A0 must be at V_{IH} for TMS 4108-1

$\overline{RAS}$-only refresh timing



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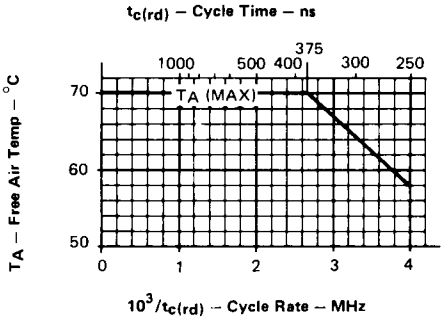
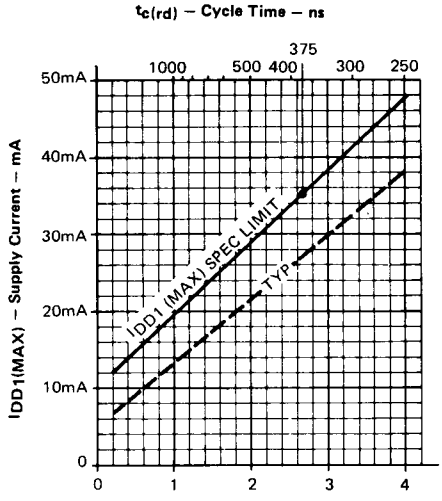
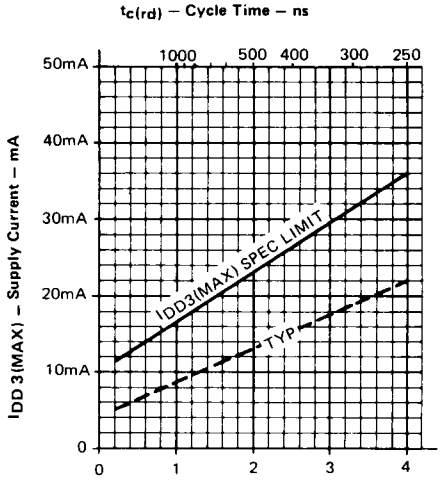
CYCLE RATE (& TIME) VS TEMPERATURE



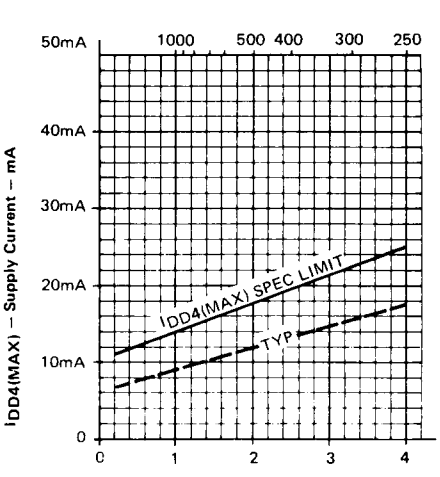
CYCLE RATE (& TIME) vs MAX SUPPLY CURRENT, I_{DD1}



CYCLE RATE (& TIME) vs MAX SUPPLY CURRENT, I_{DD3}



PAGE-MODE CYCLE RATE (& TIME) vs MAX SUPPLY CURRENT, I_{DD4}



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